

### **INCHANGE SEMICONDUCTOR**

## isc N-Channel MOSFET Transistor

### IXTQ50N20P

#### FEATURES · Drain Source Voltage-D(2) : V<sub>DSS</sub>= 200V(Min) Static Drain-Source On-Resistance : $R_{DS(on)} = 60m \Omega$ (Max) · Fast Switching S(3) 100% avalanche tested pin 1, Gate Minimum Lot-to-Lot variations for robust device 2, Drain performance and reliable operation 2 3 3. Source 1 TO-3PN package APPLICATIONS С s · Switch-Mode and Resonant-Mode Power Supplies DC-DC Converters AC and DC Motor Drives Robotics and Servo Controls ė ABSOLUTE MAXIMUM RATINGS(Ta=25°C) SYMBOL PARAMETER VALUE UNIT 200 **Drain-Source Voltage** V VDSS R Gate-Source Voltage-Continuous $\pm 20$ V $V_{\text{GS}}$ mm DIM MIN MAX **Drain Current-Continuous** 50 А $I_D$ 19.60 20.30 A 15.50 В 15.70 Drain Current-Single Plused 120 А **I**DM 4.70 4.90 С D 0.90 1 10 E 1.90 $P_D$ Total Dissipation @T<sub>C</sub>=25℃ 360 W F 3.40G 2.90Max. Operating Junction Temperature -55~175 °C Ti Н 3.20 0.595 19.80 K -55~175 °C Storage Temperature Tstg 1.90 2.20 10.89 Ν 10.9Q 4.90 THERMAL CHARACTERISTICS R 3.353.45.995 s 2.100SYMBOL PARAMETER MAX UNIT 5.90 6.20 9.90 10.10

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R<sub>th j-c</sub>

Thermal Resistance, Junction to Case

°C/W

0.42



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#### • ELECTRICAL CHARACTERISTICS

#### T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	МАХ	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> =250µA	200			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = 250uA	2.5		5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 40A			60	$m\Omega$
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =200V; V <sub>GS</sub> = 0 V <sub>DS</sub> =200V; V <sub>GS</sub> = 0;TJ=175℃			25 250	μA
V <sub>SD</sub>	Diode Forward On-voltage	I <sub>F</sub> = 50A ;V <sub>GS</sub> = 0			1.5	V

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